

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	3119	iii-v and epitax\$4 and silicon	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 11:30
2	BRS	L2	0	1 and 247/\$.ccls.	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 11:23
3	BRS	L3	2179	1 and 257/\$.ccls.	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 11:23
4	BRS	L4	6894	gaas and epitax\$4 and silicon	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 11:27
5	BRS	L5	3999	gaas and epitaxy and silicon	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 11:30
6	BRS	L6	2722	5 and 257/\$.ccls.	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 11:28

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L7	1251	6 and laser	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 11:28
8	BRS	L8	1075	7 and @ay<2000	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 11:29
9	BRS	L9	804	iii-v and epitax\$4 and (silicon adj substrate)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 11:30
10	BRS	L10	586	9 and 257/\$.ccls.	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 11:43
11	BRS	L11	273	10 and ((light adj emitting adj diode) laser)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 11:44

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1	BRS	L1	1919	(light adj emitting adj diode) and coherent	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 10:15
2	BRS	L2	173	1 and 257/\$.ccls.	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 10:21
3	BRS	L3	1084	(porous adj silicon) and light	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 10:31
4	BRS	L4	423	3 and 257/\$.ccls.	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 10:21
5	BRS	L5	474	(porous adj silicon) and laser	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 10:33
6	BRS	L6	2	porous adj silicon adj laser	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 10:34

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7	BRS	L7	94	(porous adj silicon) and (light adj emitting adj diode)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/11/05 10:34